Dual P-Channel 30-V (D-S) MOSFET

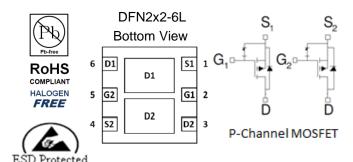
Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

Typical	Δnn	lications:
i ypicai	Thh	nications.

- · Load switches
- Low power buck/boost converters
- · Power routing in battery powered devices

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-30	220 @ V _{GS} = -4.5V	-2.2		
-30	300 @ V _{GS} = -2.5V	-1.9		



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Symbol	Limit	Units	
Drain-Source Voltage			V_{DS}	-30	V	
Gate-Source Voltage			V_{GS}	±8	V	
Continuous Drain Coursent®		Γ _A =25°C	. 1	-2.2	А	
Continuous Drain Current ^a	T	Г _А =70°С	I _D	-1.7		
Pulsed Drain Current ^b				-10		
Continuous Source Current (Diode Conduction) a			Is	-1.7	Α	
Dower Discipation 8	T _A =25°C T _A =70°C		P _D	1.5	W	
Power Dissipation ^a			гD	0.95	V V	
Operating Junction and Storage Temperature Range				-55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a			83	°C/W			
Maximum Junction-to-Ambient			120	C/VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

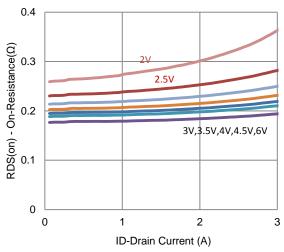
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.3			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-4			Α	
Dunin Course On Braintana a	r	$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$			220	mO.	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -1.6 \text{ A}$			300	mΩ	
Forward Transconductance a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A}$		22		S	
Diode Forward Voltage ^a		V_{SD} $I_{S} = -0.9 \text{ A}, V_{GS} = 0 \text{ V}$		-0.84		V	
		Dynamic ^b					
Total Gate Charge	Q_g	Q_g $V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		4			
Gate-Source Charge	Q_{gs}	$I_{DS} = -13 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -2 \text{ A}$		0.9		nC	
Gate-Drain Charge	Q_{gd}	10 - 2 A		0.9			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -15 \text{ V}, R_{L} = 7.5 \Omega,$		7			
Rise Time	t_r $I_D = -2 A$,			10]	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		28		ns	
Fall Time	t _f	V GEN = 4.3 V, NGEN = 0 12		16			
Input Capacitance	C _{iss}			190			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		22		pF	
Reverse Transfer Capacitance	C _{rss}			18			

Notes

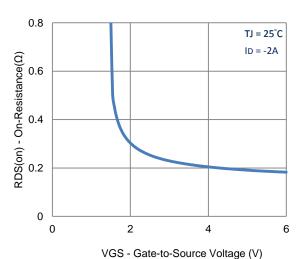
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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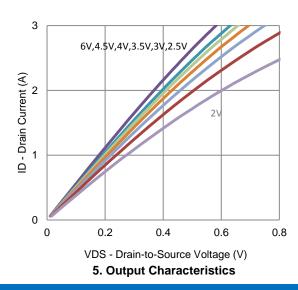
Typical Electrical Characteristics

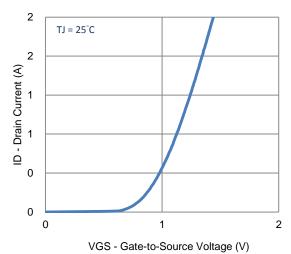


1. On-Resistance vs. Drain Current

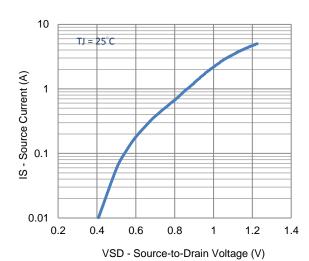


3. On-Resistance vs. Gate-to-Source Voltage

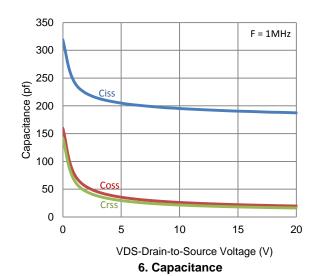




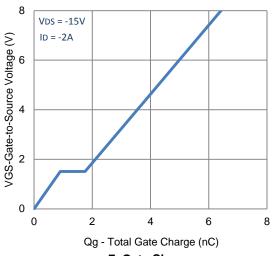
2. Transfer Characteristics

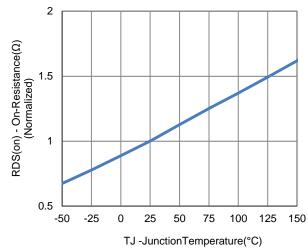


4. Drain-to-Source Forward Voltage



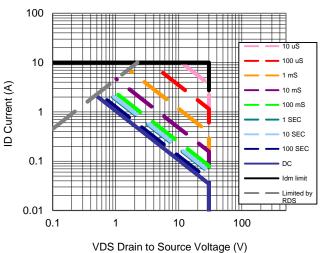
Typical Electrical Characteristics

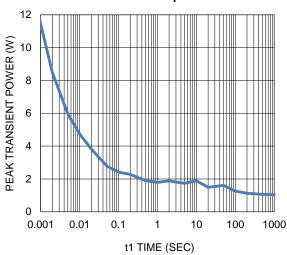






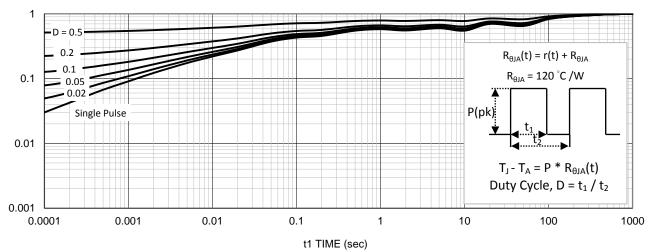






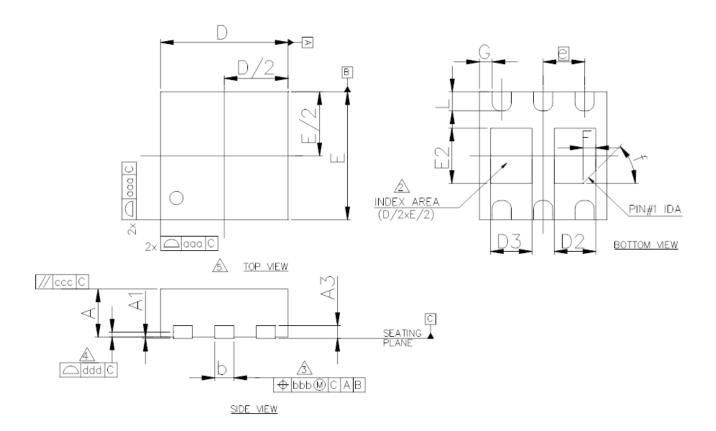
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES					
	MIN.	NOM.	MAX.	П	MIN.	NOM.	MAX.		
A	0.70	0.75	0.80	П	0.028	0.030	0.032		
A1	0.00	0.02	0.05	П	0.000	0.001	0.002		
A.3		0.20 ref		П		[0.008 ref]			
ь	0.25	0.30	0.35	П	0.010	0.012	0.014		
D	2.00 BSC			П	0.079 BSC				
D2	0.60	0.65	0.70	П	0.024	0.026	0.028		
D3	0.60	0.65	0.70	П	0.024	0.026	0.028		
E	2.00 BSC			П	0.079 BSC				
E2	0.81	0.86	0.91	П	0.032	0.034	0.036		
<u>e</u>	0	.65_BSC		П		0.026 BSC			
L	0.25	0.30	0.35	П	0.010	0.012	0.014		
F	C).20 REF		П	0.008 REF				
f		45?		П		45?			
G	0.15	0.20	0.25	П	0.006	0.008	0.010		
aaa		0.15		П		0.006			
bbb	0.10				0.004				
ccc	0.10				0.004				
ddd	0.08				0.003				